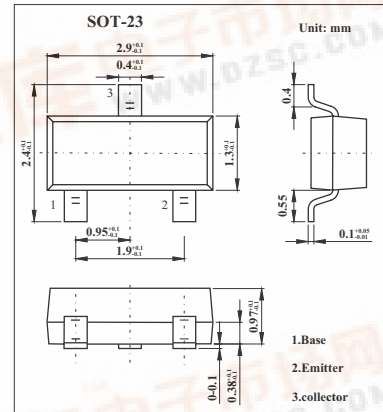


SMD Type Transistors

Silicon NPN Epitaxial  
2SC3120

Features

- 



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	15	V
Emitter-base voltage	V <sub>EBO</sub>	3	V
Collector current	I <sub>C</sub>	50	mA
Base current	I <sub>B</sub>	25	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>J</sub>	125	°C
Storage temperature Range	T <sub>stg</sub>	-55 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 2V, I <sub>C</sub> = 0			1.0	μA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	15			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5 mA	40	100	200	
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		0.6	0.9	pF
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 2mA	1500	2400		MHz
Conversion Gain	G <sub>ce</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 2mA, f = 800MHz	12	17		dB
Noise Figure	NF	F <sub>L</sub> = 830MHz		8		dB

Marking

Marking	HB
---------	----

